DECLARATION AND POWER OF ATTORNEY

As a below named inventor. I hereby declare that:

My residence, post office address, and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter claimed and for which a patent is sought on the invention entitled:

VIA/LIN	IE INDUCTOR	ON SEMICONDUCTOR M	IATERIAL
the specification of	which		
is attached here	to		
was filed on as Application Serial No and was amended on			
		and understand the contents as amended by any amendmen	
of America before and that the same v than one year prior	this invention the vas not in public to this applicati me to be material	e same was ever known or us ereof or more than one year p use or on sale in the United S ion. I acknowledge the duty of I to patentability in accordance	rior to this application, states of America more to disclose information
119(a)-(d) or Secti certificate, or Secti least one country of below any foreign	ion 365(b) of a on 365(a) of any other than the U application for	nefits under Title 35, United my foreign application(s) for PCT international application inited States, listed below ar patent or inventor's certification ich priority is claimed:	r patent or inventor's on which designated at d have also identified
Prior Foreign App	olication(s):		
<u>Number</u>	Country	Day/Month/Year filed	Priority Claimed <u>Yes</u> <u>No</u>
I hereby claim the bapplication(s) listed		USC 119(e) of any United Sta	ites provisional
Prior Provisional	Application(s):		
Application Numb	<u>er</u> <u>Filin</u>	g Date	

I hereby claim the benefit under Title 35, United States Code, Section 120 of any United States application(s), or Section 365(c) of any PCT international application designating the United States, listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States or PCT international application in the manner provided by the first paragraph of Title 35, United States Code. Section 112. I acknowledge the duty to disclose material information as defined in Title 37, Code of Federal Regulations, Section 1.56 which occurred between the

filing date of the prior application and the national or PCT international filing date of this application:

Prior U.S. Application(s):

Serial No.

Filing Date

Status: Patented, Pending, Abandoned

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

I hereby revoke any previous Powers of Attorney and appoint the following attorney(s) and/or agent(s), each said individual being a member or associate of The Law Offices of Mikio Ishimaru or being employed by Chartered Semiconductor Manufacturing Ltd.:

Mikio Ishimaru

Reg. No. 27,449

for so long as they remain with such law offices or company with full power of substitution and revocation, to prosecute this application and to transact in connection therewith all business in the U.S. Patent and Trademark Office and before competent International Authorities; said appointment to be to the exclusion of myself and my other attorney(s); and all future correspondence should be addressed to:

> Mikio Ishimaru The Law Offices of Mikio Ishimaru 1110 Sunnyvale-Saratoga Rd., Suite A1 Sunnyvale, California 94087

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